



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Features

- Epitaxial Planar Die Construction
- Ultra-Small Leadless Surface Mount Package
- Ideally Suited for Automated Assembly Processes

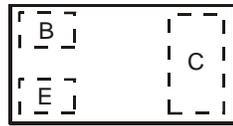
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - NiPdAu
Solderable per MIL-STD-202, Method 208 
- Weight: 0.0009 grams (Approximate)

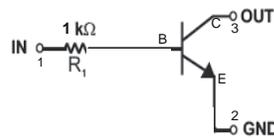
X1-DFN1006-3



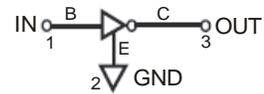
Bottom View



Top View
Pin-Out



Device Symbol



Equivalent Inverter
Circuit

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-5 to +10	V
Output Current (I _o)	I _{C(MAX)}	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	250	mW
Power Derating above +25°C	P _{der}	2	mW/°C
Thermal Resistance, Junction to Ambient Air (Note 5) (Equivalent to one heated junction of NPN)	R _{θJA}	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Collector-Base Breakdown Voltage	BV _{CBO}	50	—	—	V	I _C = 50μA, I _E = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	50	—	—	V	I _C = 1mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	5	—	—	V	I _E = 50μA, I _C = 0
Collector-Base Cutoff Current	I _{CBO}	—	—	0.1	μA	V _{CB} = 50V, I _E = 0
Emitter-Base Cutoff Current	I _{EBO}	—	—	0.1	μA	V _{EB} = 4V, I _C = 0
ON CHARACTERISTICS (Note 6)						
DC Current Gain	h _{FE}	100	380	600	—	V _{CE} = 5V, I _C = 1mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	0.25	V	I _C = 50mA, I _B = 2.5mA
Input Resistance	R ₁	0.7	1	1.3	kΩ	—
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	—	250	—	MHz	V _{CE} = 10V, I _E = 5mA, f = 100MHz

- Notes:
5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 6. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

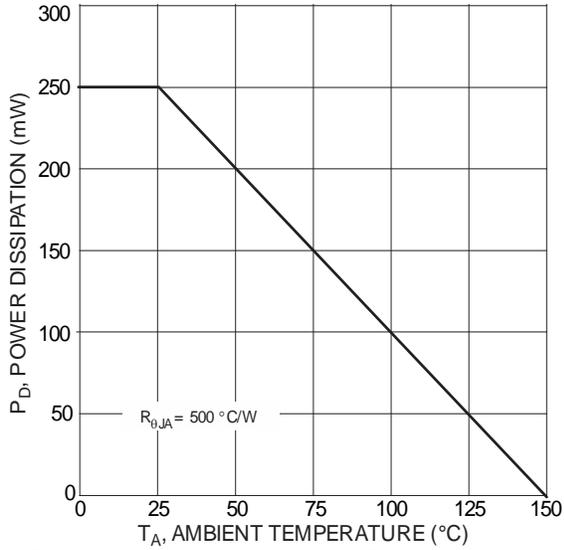


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 5)

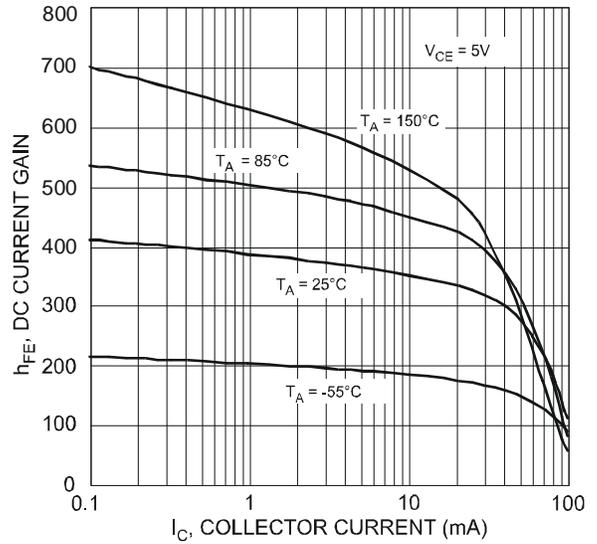


Fig. 2 Typical DC Current Gain vs. Collector Current

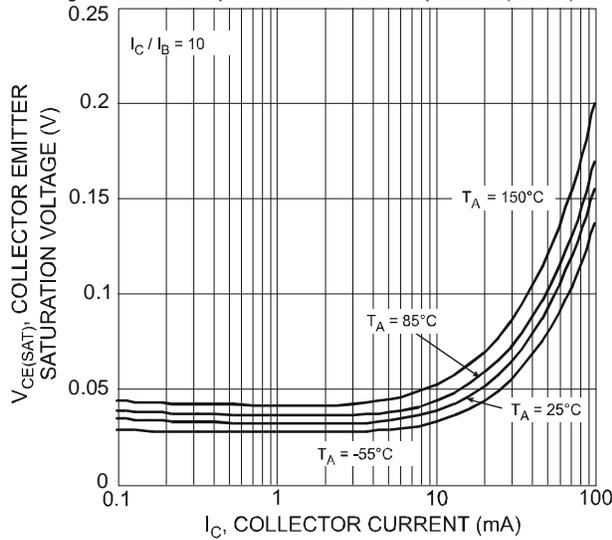


Fig. 3 Typical Collector Emitter Saturation Voltage vs. Collector Current

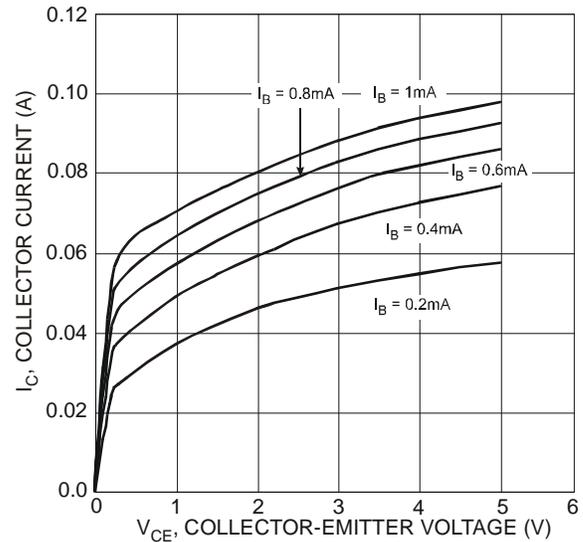


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

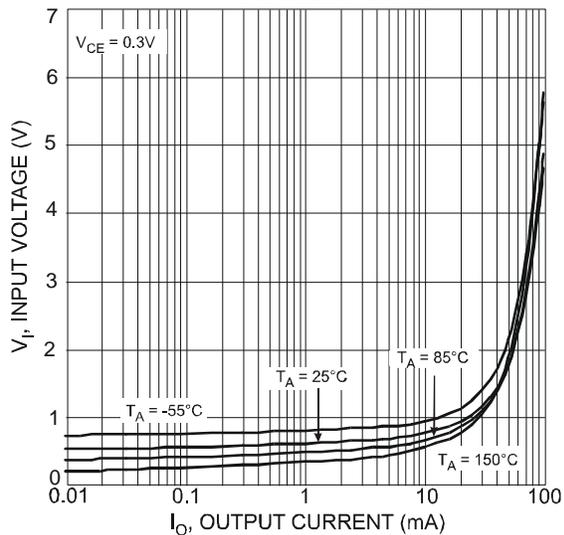


Fig. 5 Typical Input Voltage vs. Output Current (On Characteristics)

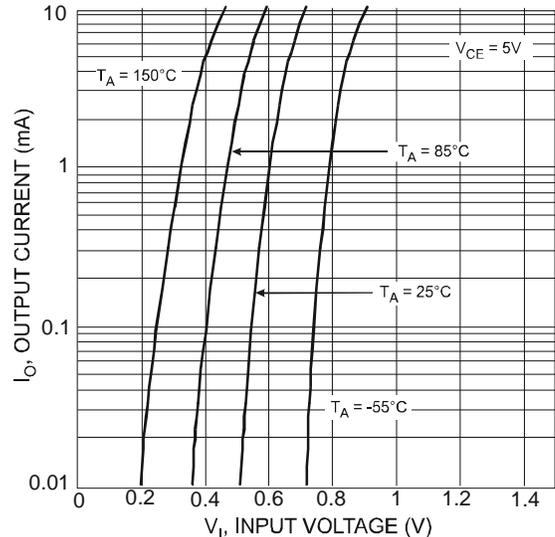
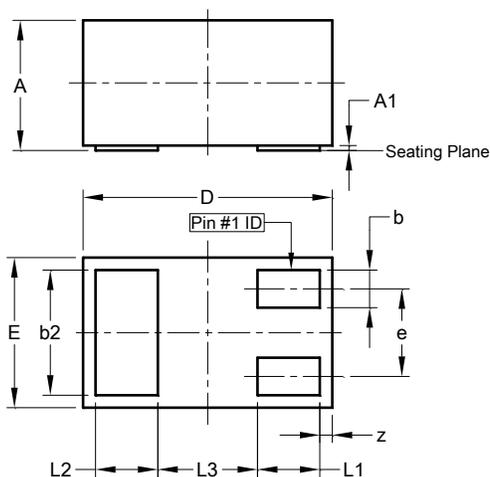


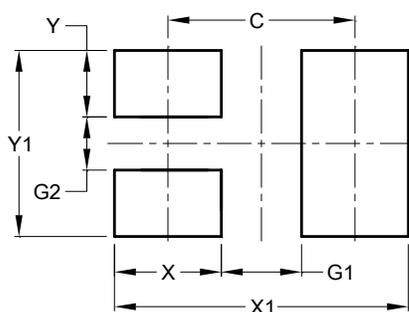
Fig. 6 Typical Output Current vs. Input Voltage (Off Characteristics)

Package Outline Dimensions



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70